

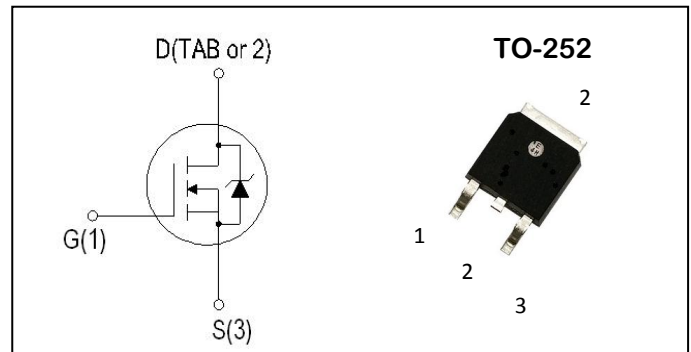
N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V_{DSS}	I_D	$R_{DS(ON)}$ (m Ω)
30V	70A	4.9m Ω @ $V_{GS}=10V$

Features:

- Low Gate Charge for Fast Switching Application
- Low $R_{DS(ON)}$ to Minimize Conductive Loss
- 100% EAS Guaranteed
- Optimized $V_{(BR)DSS}$ Ruggedness
- Lead-Free,RoHS Compliant



Description:

The ADM3080E uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Ratings	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		± 15V	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	70	A
Mounted on Large Heat Sink				
I _{DM}	300μs Pulse Drain Current Tested ⁽²⁾	T _C =25°C	300	A
I _D	Continuous Drain Current ⁽¹⁾	T _C =25°C	70	A
		T _C =100°C	50	A
P _D	Maximum Power Dissipation	T _C =25°C	70	W

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
R_{thJC}	Thermal resistance junction-case max ⁽¹⁾	2.0	$^\circ\text{C/W}$
R_{thJA}	Thermal resistance junction-ambient max ⁽¹⁾	65	$^\circ\text{C/W}$

Electrical Characteristics (TA=25°C Unless Otherwise Noted)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
On/off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250uA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V , T _J =25°C	--	--	1.0	uA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250uA	1.0	1.6	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =± 15V, V _{DS} =0V	--	--	± 100	nA
R _{DS(ON)}	Drain-SourceOn-stateResistance ⁽²⁾	V _{GS} = 10V, I _{DS} =25A	--	4	4.9	mΩ
		V _{GS} = 4.5V, I _{DS} =20A	--	5.1	6.6	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0V,	--	2200	--	pF
C _{OSS}	Output Capacitance	V _{DS} =15V,	--	370	--	
C _{rss}	Reverse Transfer Capacitance	Frequency=1MHz	--	250	--	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{DS} =15V,	--	7	--	nS
t _r	Turn-on Rise Time	I _D = 70A, V _{GS} = 10V,	--	12	--	
t _{d(OFF)}	Turn-off Delay Time	R _{GEN} =2.7 Ω	--	26	--	
t _f	Turn-off Fall Time		--	10	--	
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} = 10V,	--	32	--	nC
Q _{gs}	Gate-Source Charge	I _{DS} =70A	--	5	--	
Q _{gd}	Gate-Drain Charge		--	10	--	
Avalanche Characteristics						
EAS	Single Pulse Avalanche Energy ⁽³⁾	L=0.5mH I _{AS} =28A, V _{gs} = 10V, R _G =50Ω , Starting T _J = 25°C	--	--	290	mJ
Diode Characteristics						
V _{SD}	Diode Forward Voltage ⁽²⁾	I _{SD} = 70A, V _{GS} = 0	--	--	1.4	V
t _{rr}	Reverse Recovery Time	I _{SD} =70A, dI _{SD} /dt=100A/μs	--	35	--	ns
q _{rr}	Reverse Recovery Charge		--	25	--	nC

NOTES:

1. Surface Mounted on FR4 Board, t ≤ 10 sec.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 0.5%
3. The Min. value is 100% EAS tested guarantee.

Typical Performance Characteristics

Figure 1: On-Region Characteristics

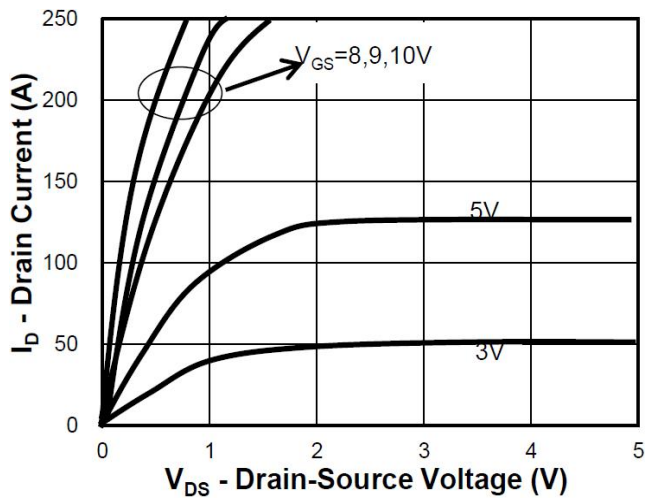


Figure 2: Power Dissipation

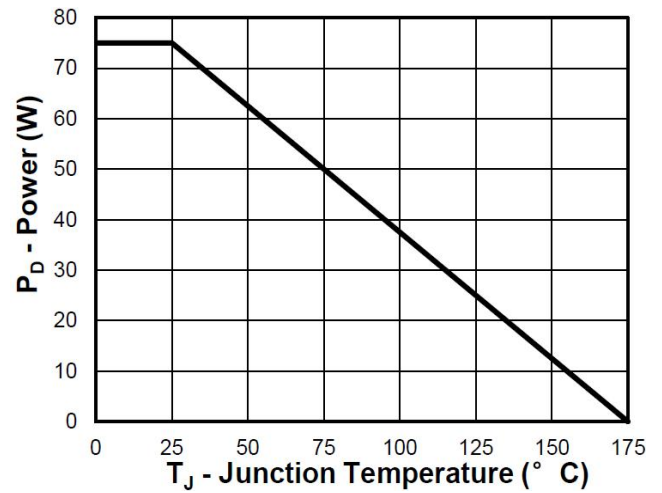


Figure 3: Maximum Drain Current vs. Case Temperature

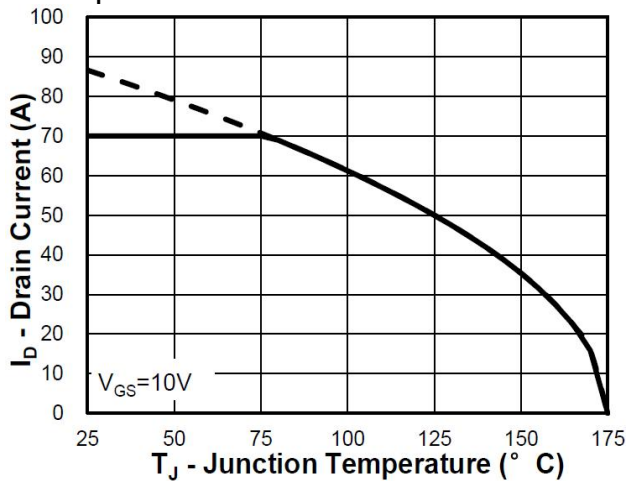


Figure 4: Drain-Source on Resistance

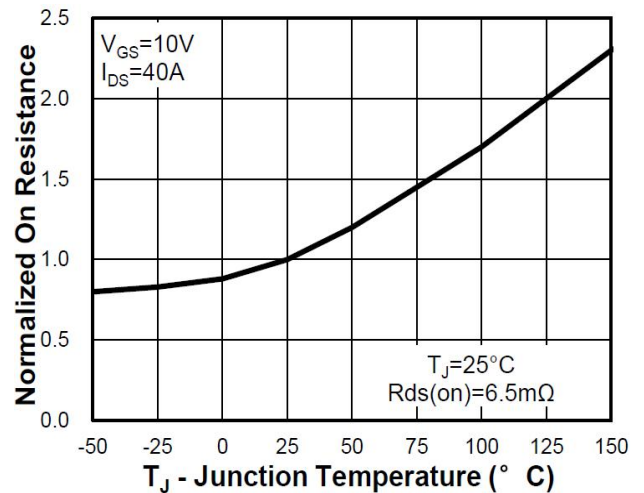


Figure 5: Source- Drain Diode Forward

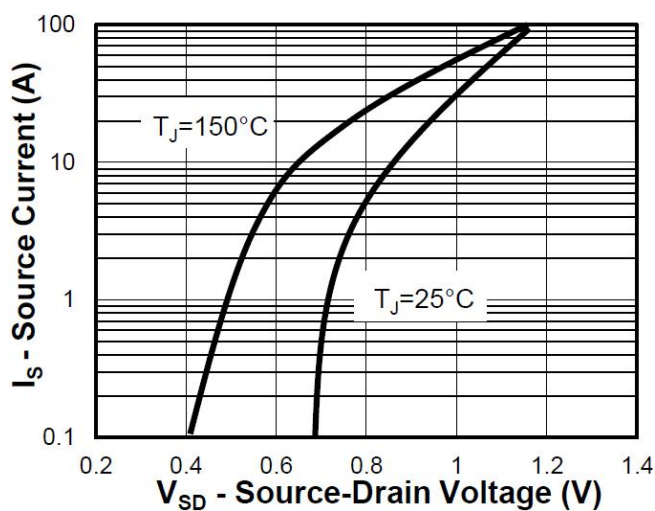


Figure 6: Gate Charge Characteristics

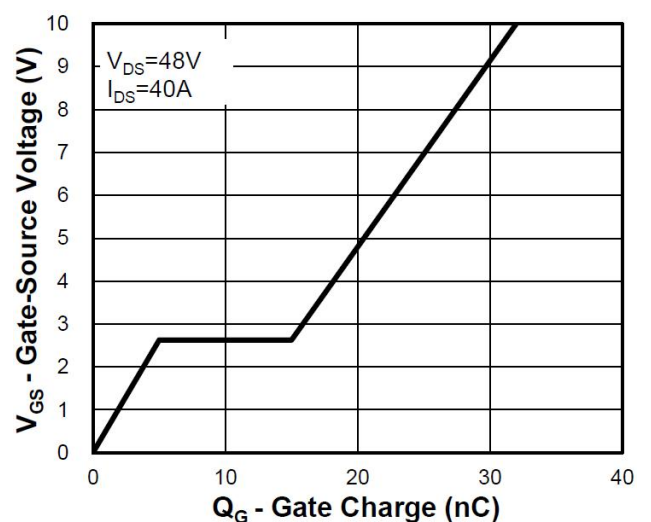


Figure 7: Capacitance vs Vds

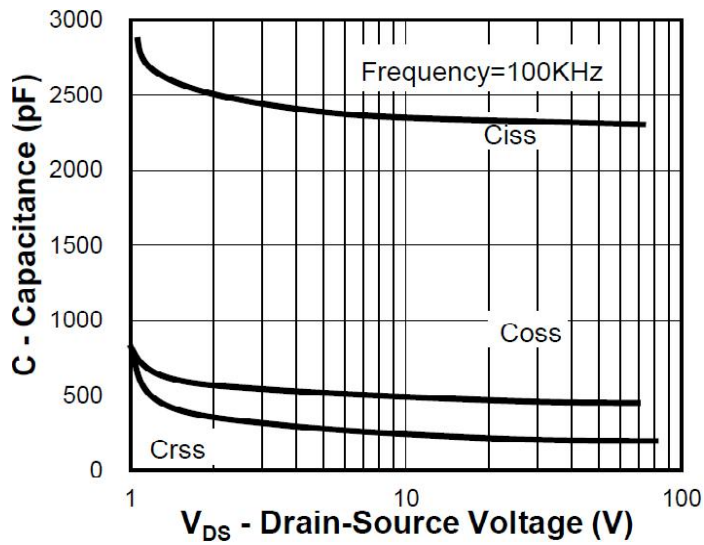


Figure 8: Safe Operation Area

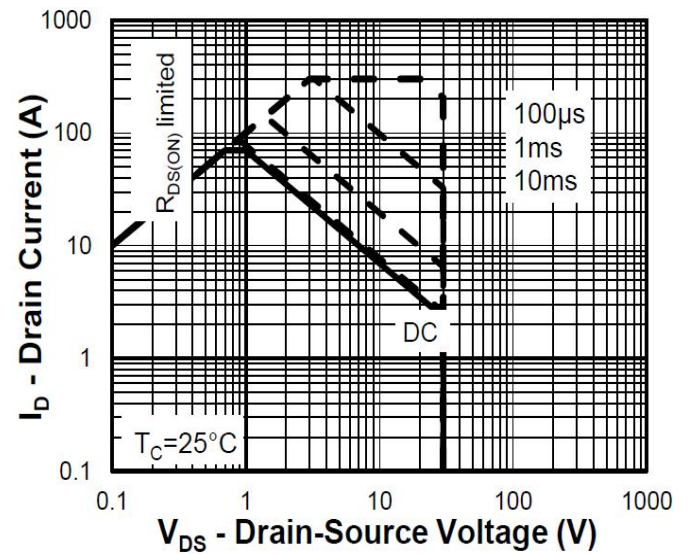
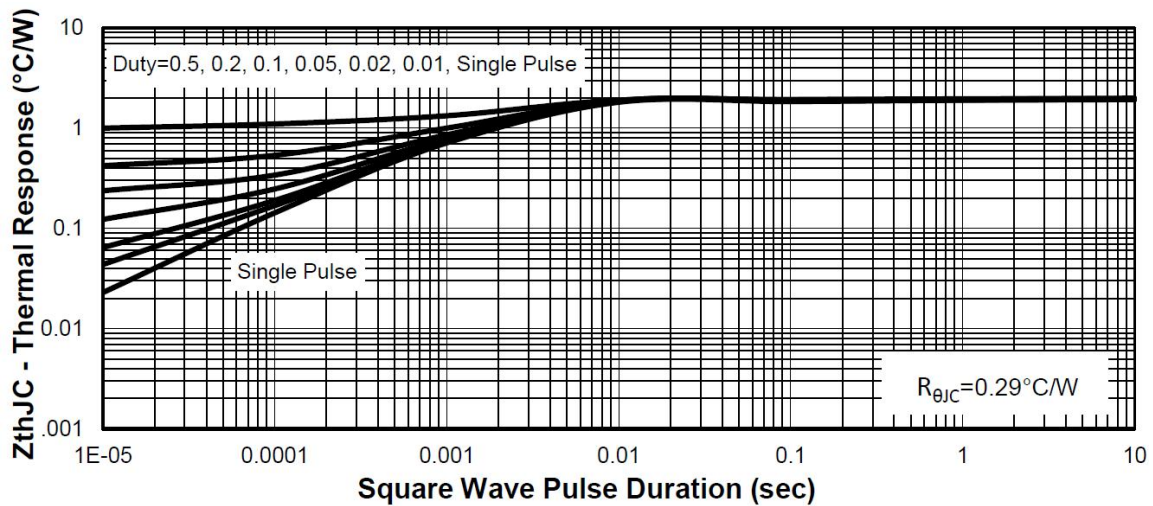
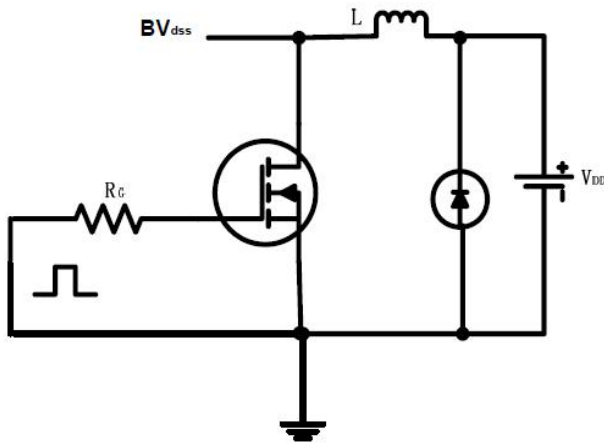


Figure 9: Transient Thermal Impedance

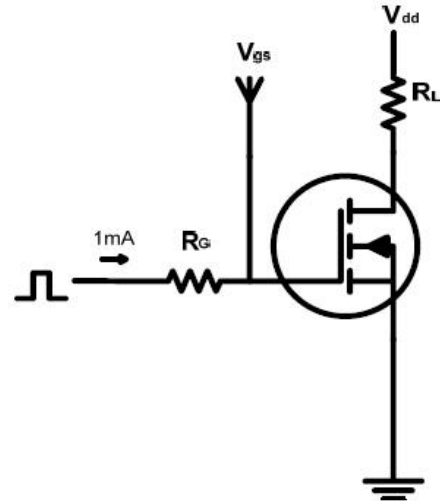


Test circuits and Waveforms

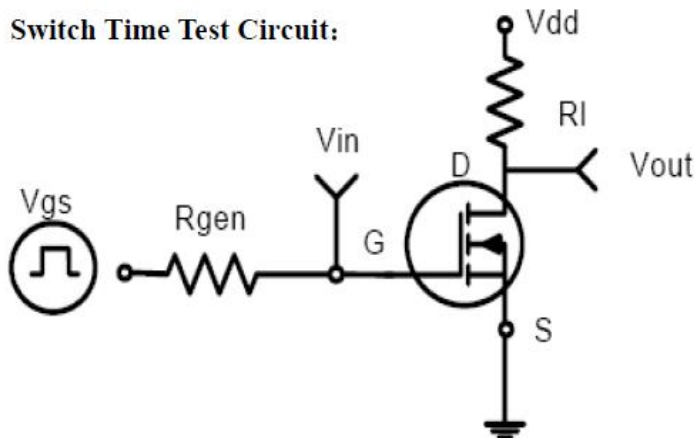
EAS test circuits:



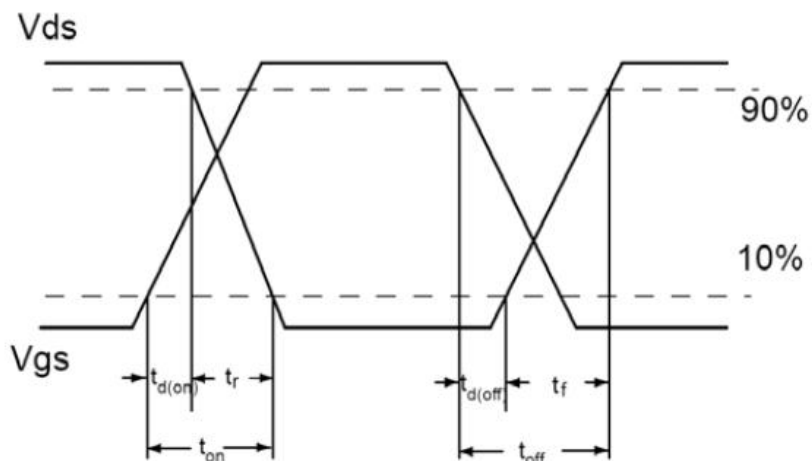
Gate charge test circuit:



Switch Time Test Circuit:

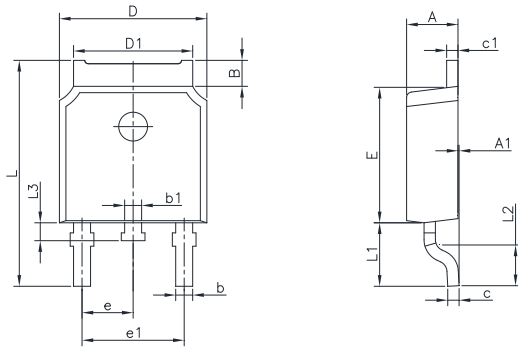


Switch Waveforms:



PACKAGE MECHANICAL DATA

TO-252-2 Package Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.070	1.220	0.042	0.048
b	0.720	0.850	0.028	0.033
b1	0.720	0.850	0.028	0.033
c	0.450	0.620	0.017	0.024
c1	0.450	0.620	0.017	0.024
D	6.350	6.800	0.250	0.280
D1	5.200	5.500	0.205	0.220
E	5.900	6.200	0.232	0.244
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	10.60	0.374	0.396
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035

Ordering information

Part number	Package	Marking	Packing	Quantity
ADM3080E	TO-252-2	ADM3080E	Tube	80pcs
			Embossed tape	2500pcs

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